



查询"CEB80N75"供应商

CEP80N75/CEB80N75

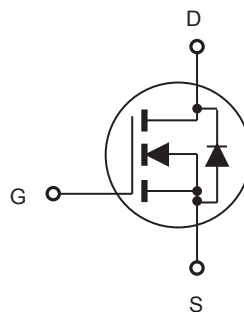
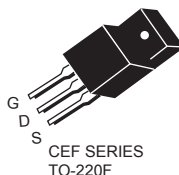
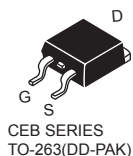
CEF80N75

N-Channel Enhancement Mode Field Effect Transistor

FEATURES

Type	V _{DSS}	R _{DS(ON)}	I _D	@V _{GS}
CEP80N75	75V	13mΩ	80A	10V
CEB80N75	75V	13mΩ	80A	10V
CEF80N75	75V	13mΩ	80A ^e	10V

- Super high dense cell design for extremely low R_{DS(ON)}.
- High power and current handling capability.
- Lead free product is acquired.
- TO-220 & TO-263 & TO-220F full-pak for through hole.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Limit		Units
		TO-220/263	TO-220F	
Drain-Source Voltage	V _{DS}	75		V
Gate-Source Voltage	V _{GS}	±20		V
Drain Current-Continuous	I _D	80	80 ^e	A
Drain Current-Pulsed ^a	I _{DM} ^f	320	320 ^e	A
Maximum Power Dissipation @ $T_C = 25^{\circ}\text{C}$ - Derate above 25°C	P _D	200	75	W
		1.3	0.5	W/°C
Single Pulsed Avalanche Energy ^d	E _{AS}	880	880	mJ
Single Pulsed Avalanche Current ^d	I _{AS}	45	45	A
Operating and Store Temperature Range	T _J , T _{stg}	-55 to 175		°C

Thermal Characteristics

Parameter	Symbol	Limit		Units
Thermal Resistance, Junction-to-Case	R _{θJC}	0.75	2	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.5	65	°C/W

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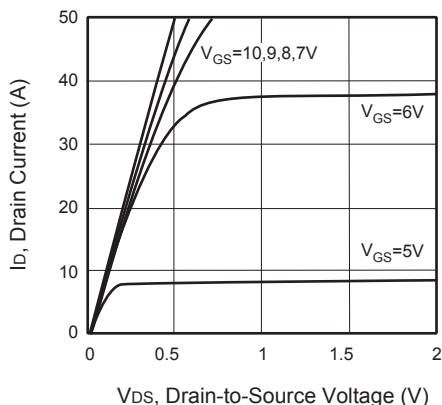


Figure 1. Output Characteristics

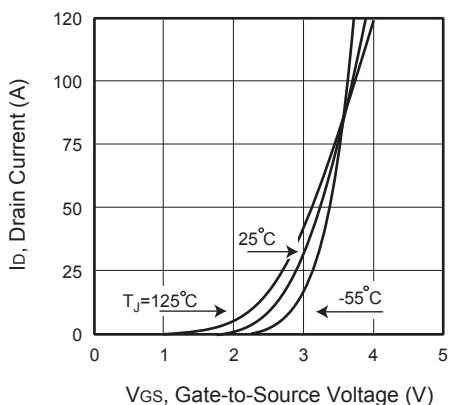


Figure 2. Transfer Characteristics

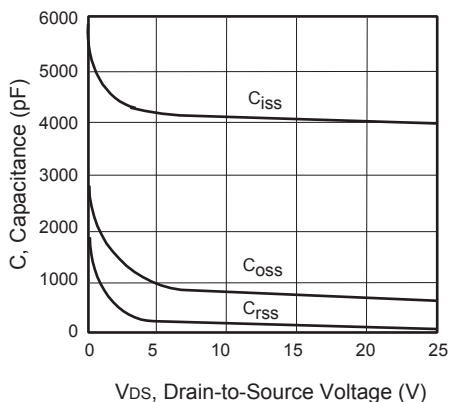


Figure 3. Capacitance

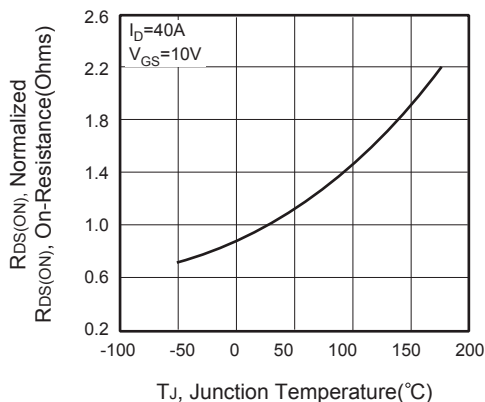


Figure 4. On-Resistance Variation with Temperature

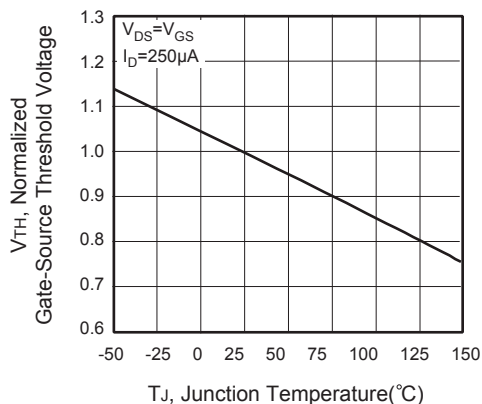


Figure 5. Gate Threshold Variation with Temperature

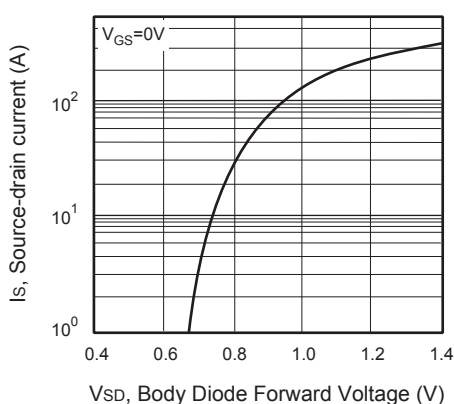


Figure 6. Body Diode Forward Voltage Variation with Source Current



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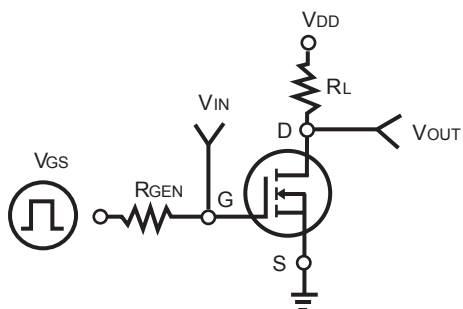
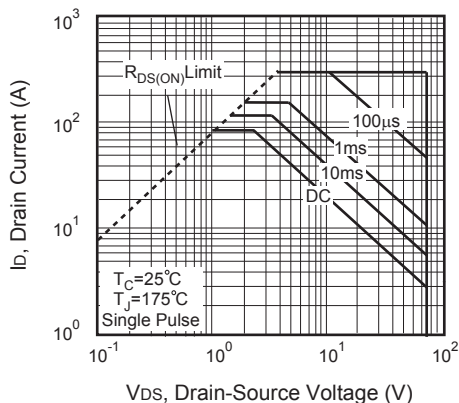
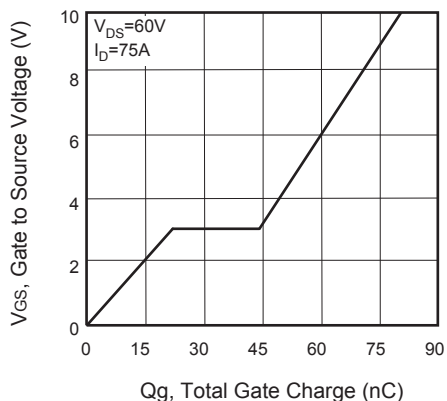


Figure 9. Switching Test Circuit

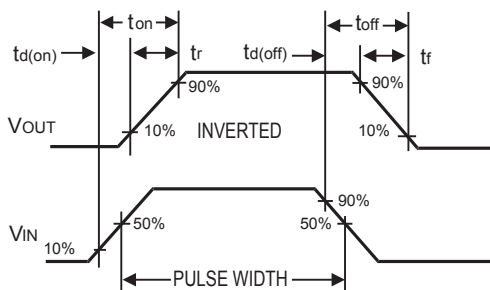


Figure 10. Switching Waveforms

